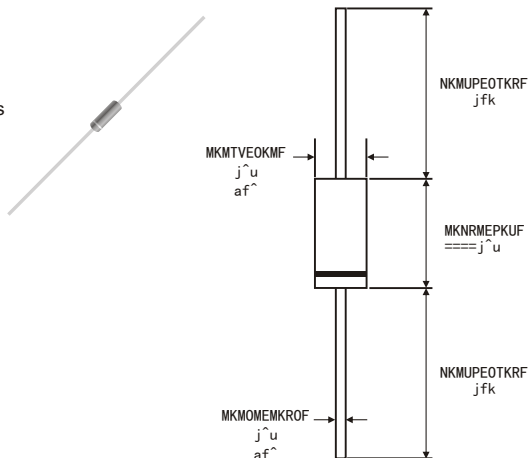


FEATURES

- Metal-on-silicon junction
 - Low turn-on voltage
 - Ultrafast switching speed
 - Primarily intended for high level UHF mixers and ultrafast switching applications
- The diode is also available in the MiniMELF case with type designation LL19.
- High temperature soldering guaranteed: 260°C/10 seconds at terminals
 - Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

DO-35



Dimensions in inches and (millimeters)

MECHANICAL DATA

- Case: DO-35 glass case
- Polarity: color band denotes cathode end
- Weight: Approx. 0.13 gram

ABSOLUTE RATINGS(LIMITING VALUES)

	Symbols	Value	Units
Peak Reverse Voltage	V _{RRM}	10	V
Forward Continuous Current	I _F	30	mA
Surge non repetitive forward current t _p ≤ 1s	I _{FSM}	60	mA
Junction and Storage temperature range	T _{STG}	-65 to +150	°C
	T _J	-65 to +150	°C
Maximum Lead Temperature for Soldering during 10s at 4mm from Case	T _L	230	°C

ELECTRICAL CHARACTERISTICS

	Symbols	Min.	Typ.	Max.	Units
Reverse breakover voltage at I _R =10μA	V _R	10			V
					V
Leakage current at V _R =5V	I _R			100	nA
Forward voltage drop at I _F =1mA Test pulse: t _p ≤ 300μs δ < 2% I _F =35mA	V _F			0.40	V
				1.0	V
Junction Capacitance at V _R =0V, f=1GHz	C _J			1.2	pF
Thermal resistance	R _{θJA}			400	K/W

RATINGS AND CHARACTERISTICS CURVES

Figure 1. Forward current versus forward voltage at low level (typical values)

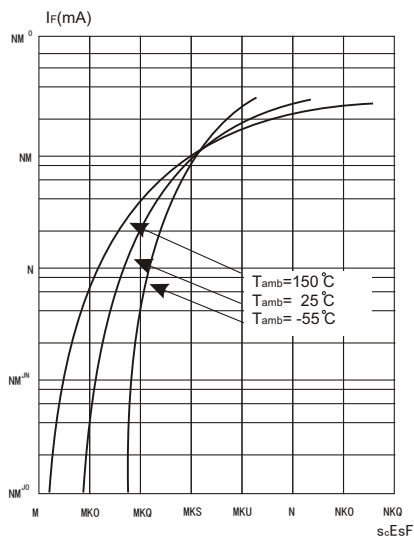


Figure 2. Capacitance C versus reverse applied voltage Vr (typical values)

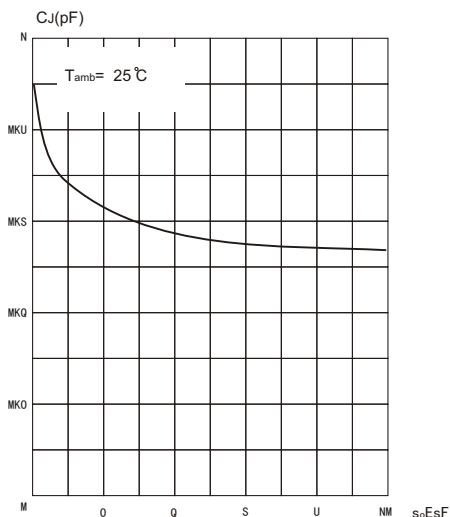


Figure 3. Reverse current versus ambient temperatures

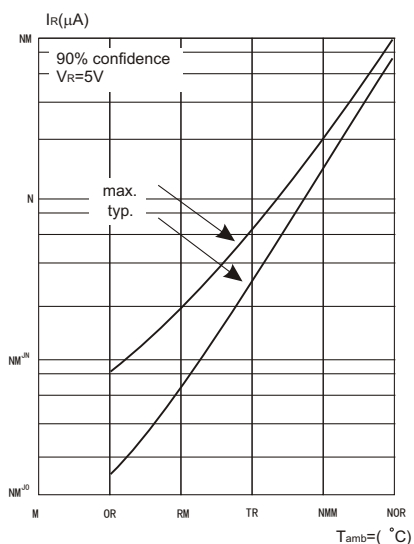


Figure 4. Reverse current versus continuous Reverse voltage (typical values)

